

## SD103AWS - SD103CWS

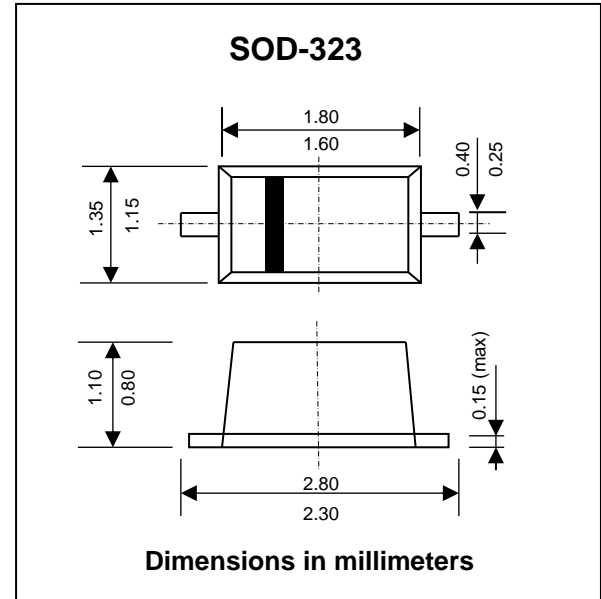
### FEATURES :

- \* For general purpose applications
- \* The SD103 series is a metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring.
- \* The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.
- \* These diodes are also available in the MiniMELF case with type designations LL103A thru LL103C.
- \* Pb / RoHS Free

### MECHANICAL DATA :

- \* Case : SOD-323 plastic Case
- \* Weight : approx. 0.004 g
- \* SD103AWS Marking Code : S4
- \* SD103BWS Marking Code : S4
- \* SD103CWS Marking Code : S4

## SCHOTTKY BARRIER DIODES



### Maximum Ratings and Thermal Characteristics (T<sub>C</sub> = 25 °C unless otherwise noted)

| Parameter                                    | Symbol             | Value              | Unit |
|--|--------------------|--------------------|------|
| Repetitive Peak Reverse Voltage              | SD103AWS           | 40                 | V    |
|  | SD103BWS           | 30                 |      |
|  | SD103CWS           | 20                 |      |
| Average Forward Rectified Current            | I <sub>F(AV)</sub> | 350                | mA   |
| Maximum Single Cycle Surge 10 μs Square Wave | I <sub>FSM</sub>   | 2                  | A    |
| Power Dissipation (Infinite Heat Sink)       | P <sub>tot</sub>   | 150 <sup>(1)</sup> | mW   |
| Thermal Resistance Junction to Ambient Air   | R <sub>θJA</sub>   | 650 <sup>(1)</sup> | °C/W |
| Junction Temperature                         | T <sub>J</sub>     | 125 <sup>(1)</sup> | °C   |
| Storage temperature range                    | T <sub>STG</sub>   | -55 to + 150       | °C   |

### Electrical Characteristics (T<sub>J</sub> = 25°C unless otherwise noted)

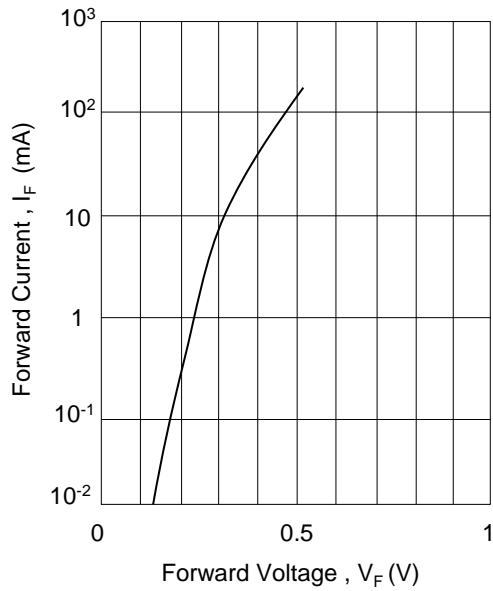
| Parameter             | Symbol           | Test Condition  | Min | Typ | Max  | Unit |
|-----------------------|------------------|---|-----|-----|------|------|
| Reverse Current       | SD103AWS         | V <sub>R</sub> = 30 V   | -   | -   | 5    | μA   |
|                       | SD103BWS         | V <sub>R</sub> = 20 V   | -   | -   | 5    |      |
|                       | SD103CWS         | V <sub>R</sub> = 10 V   | -   | -   | 5    |      |
| Forward Voltage Drop  | V <sub>F</sub>   | I <sub>F</sub> = 20mA   | -   | -   | 0.37 | V    |
|                       |                  | I <sub>F</sub> = 200mA  | -   | -   | 0.60 |      |
| Junction Capacitance  | C <sub>tot</sub> | V <sub>R</sub> = 0 V, f = 1MHz  | -   | 50  | -    | pF   |
| Reverse Recovery Time | T <sub>rr</sub>  | I <sub>F</sub> = I <sub>R</sub> = 50mA to 200mA<br>recover to 0.1I <sub>R</sub> | -   | 10  | -    | ns   |

#### Note:

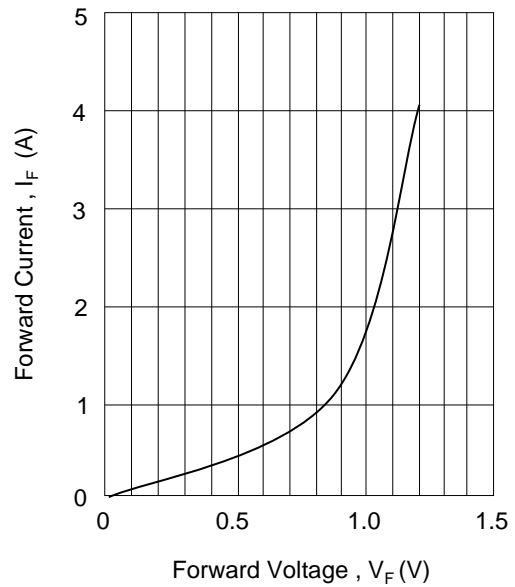
- (1) Valid provided that electrodes are kept at ambient temperature.

**RATING AND CHARACTERISTIC CURVES ( SD103AWS - SD103CWS )**

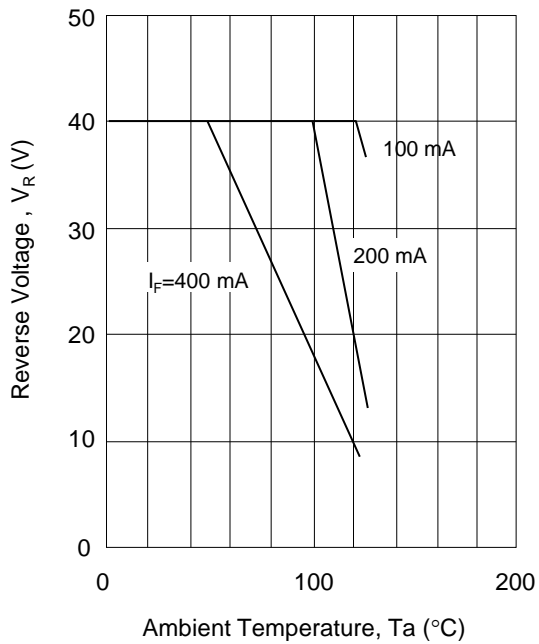
**Typical variation of forward current vs. forward voltage for primary conduction through the schottky barrier**



**Typical high current forward conduction curve  
 $t_p = 300ms$ , duty cycle = 2%**



**Blocking voltage deration versus temperature at various average forward currents**



**Typical variation of reverse current at various temperatures**

